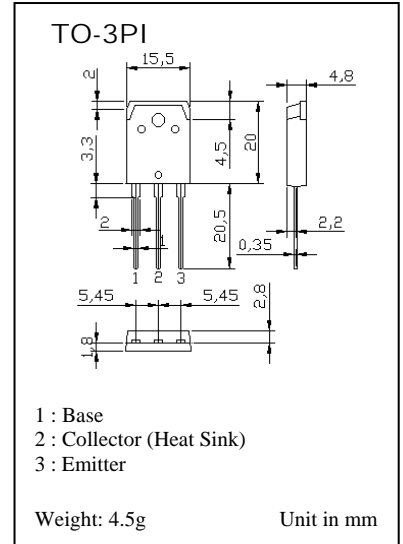


# PNP SILICON EPITAXIAL PLANAR TRANSISTOR

...designed for 140V/12A AF 60W output application.  
 ...complementary to PMD1047.

## MAXIMUM RATINGS (Ta= 25 °C)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V <sub>CB0</sub>	-160	V
Collector Emitter Voltage	V <sub>CEO</sub>	-140	V
Emitter Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current	I <sub>C</sub>	-12	A
Collector Current (Pulse)	I <sub>CP</sub>	-15	A
Collector Power Dissipation T <sub>c</sub> = 25 °C	P <sub>c</sub>	100	W
Junction Temperature	T <sub>j</sub>	-150	°C
Storage Temperature Range	T <sub>stg</sub>	-40 ~ 150	°C



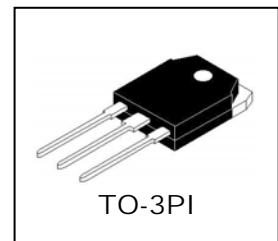
## ELECTRICAL CHARACTERISTICS (Ta= 25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> = -80V, I <sub>E</sub> = 0	-	-	-0.1	mA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V, I <sub>C</sub> = 0	-	-	-0.1	mA
DC Current Gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -1A	60	-	200	-
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -6A	20	-	-	-
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -1A	-	15	-	MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, f = 1MHz	-	300	-	pF

PNP SILICON  
 EPITAXIAL  
 PLANAR  
 TRANSISTOR

## CLASSIFICATIONS OF h<sub>FE(1)</sub>

Rank	D	E
Range	60 to 120	100 to 200



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